## Masatoshi Tanaka

List of Publications by Year in descending order

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Μλελτοςμι Τλυλκλ

#	Article	IF	CITATIONS
1	Phonon Properties of Few-Layer Crystals of Quasi-One-Dimensional ZrS <sub>3</sub> and ZrSe <sub>3</sub> . Journal of Physical Chemistry C, 2016, 120, 4653-4659.	3.1	41
2	Tensile-Strained GeSn Metal–Oxide–Semiconductor Field-Effect Transistor Devices on Si(111) Using Solid Phase Epitaxy. Applied Physics Express, 2013, 6, 101301.	2.4	40
3	Raflectance Spectra and Band Structures of Quasi-One-Dimensional [Pt(en)2][Pt(en)2X2](ClO4)4(X=I) Tj ETQq1	1 0.7843 1.6	14 rgBT /Ov
4	Development of an Apparatus for High-Resolution Auger Photoelectron Coincidence Spectroscopy (APECS) and Electron Ion Coincidence (EICO) Spectroscopy. Journal of the Vacuum Society of Japan, 2008, 51, 749-757.	0.3	14
5	SiO2/Si interfaces on high-index surfaces: Re-evaluation of trap densities and characterization of bonding structures. Applied Physics Letters, 2011, 98, 092906.	3.3	14
6	Ultrathin GeSn p-channel MOSFETs grown directly on Si(111) substrate using solid phase epitaxy. Japanese Journal of Applied Physics, 2015, 54, 04DA07.	1.5	14
7	Characterization of Effective Mobility and Its Degradation Mechanism in MoS2MOSFETs. IEEE Nanotechnology Magazine, 2016, 15, 651-656.	2.0	14
8	Photoinduced charge transfer from vacuum-deposited molecules to single-layer transition metal dichalcogenides. Japanese Journal of Applied Physics, 2016, 55, 065201.	1.5	13
9	Recent progress in coincidence studies on ion desorption induced by core excitation. Journal of Physics Condensed Matter, 2006, 18, S1389-S1408.	1.8	12
10	Surface-site-selective study of valence electronic states of a clean Si(111)-7×7 surface using SiL23VVAuger electron and Si 2pphotoelectron coincidence measurements. Physical Review B, 2011, 83, .	3.2	12
11	monolayer transition metal dichalcogenides <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"&gt; <mml:mrow> <mml:mi>T</mml:mi> <mml:msub> <mml:mi on <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"&gt; <mml:mrow> <mml:mi>Si</mml:mi> <mml:msub> <mml:m< td=""><td>&gt;X<u>⊰/</u>mml: i</td><td>mi<sub>}2</sub>mml:m</td></mml:m<></mml:msub></mml:mrow></mml:math </mml:mi </mml:msub></mml:mrow></mml:math 	>X <u>⊰/</u> mml: i	mi <sub>}2</sub> mml:m
12	mathvariant="normal">O <mmkm>&gt;</mmkm> > <mmkmo>/</mmkmo> /// <td>ml:mi&gt; &lt; m 1.6</td> <td>ıml:m. 11</td>	ml:mi> < m 1.6	ıml:m. 11
13	Thermal Desorption Process of Bromide on Si(111) Studied by Highly Sensitive Mass Spectroscopy. Japanese Journal of Applied Physics, 2003, 42, 593-596.	1.5	11
14	Theoretical Investigation of the Reaction Pathway of O Atom on Si(001)-(2 × 1). Journal of Physical Chemistry C, 2010, 114, 15671-15677.	3.1	11
15	Optical spectra near the band edge ofZrS3andZrSe3. Physical Review B, 1993, 48, 1356-1360.	3.2	10
16	Time-evolution of thermal oxidation on high-index silicon surfaces: Real-time photoemission spectroscopic study with synchrotron radiation. Surface Science, 2012, 606, 1685-1692.	1.9	9
17	Isothermal desorption process of Cl-covered Si(111) studied by surface differential reflectivity spectroscopy. Surface Science, 2003, 527, 21-29.	1.9	8
18	Surface-Site-Selective Study of Valence Electronic Structures of Clean Si(100)-2×1 Using Si-L23VV Auger Electron–Si-2p Photoelectron Coincidence Spectroscopy. Journal of the Physical Society of Japan, 2010, 79, 064714.	1.6	8

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19	Topmost-surface-sensitive Si-2p photoelectron spectra of clean Si(100)-2×1 measured with photoelectron Auger coincidence spectroscopy. Surface Science, 2010, 604, L27-L30.	1.9	8
20	Electronic structure of α-sexithiophene ultrathin films grown on. Physical Chemistry Chemical Physics, 2018, 20, 1114-1126.	2.8	8
21	Photon-stimulated desorption from chlorinated Si(111): Etching of SiCl by picosecond-pulsed laser irradiation. Physical Review B, 2006, 73, .	3.2	7
22	Reaction Kinetics in the Rapid Oxide Growth on Si(001)-(2×1) Probed with Reflectance Difference Spectroscopy. Japanese Journal of Applied Physics, 2010, 49, 055702.	1.5	7
23	Adsorption and self-assembled structures of sexithiophene on the Si(111)-3×3-Ag surface. Journal of Chemical Physics, 2015, 142, 204701.	3.0	6
24	Deposition of ZrON thin films by reactive magnetron sputtering using a hollow cylindrical target. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	6
25	Conduction Band Structure Determined from the g-Values of the Excitons in VI B Transition Metal Dichalcogenides. Journal of the Physical Society of Japan, 1982, 51, 3888-3892.	1.6	5
26	Reflectance Difference Spectroscopy in Vacuum–Ultraviolet Range: Developing Measurement System and Applying to Characterization of SiO2/Si Interfaces. Japanese Journal of Applied Physics, 2010, 49, 022403.	1.5	5
27	Site-specific ion desorption from condensed F3SiCD2CH2Si(CH3)3 induced by Si-2p core-level ionizations studied with photoelectron photoion coincidence (PEPICO) spectroscopy, Auger photoelectron coincidence spectroscopy (APECS) and Auger electron photoion coincidence (AEPICO) spectroscopy Surface Science, 2013, 607, 174-180	1.9	5
28	Characterization of Monolayer Oxide Formation Processes on High-Index Si Surfaces by Photoelectron Spectroscopy with Synchrotron Radiation. Applied Physics Express, 2013, 6, 115701.	2.4	5
29	Time Courses and Timeâ€Resolved Spectra of Firefly Bioluminescence Initiated by Two Methods of <scp>ATP</scp> Injection and Photolysis of Caged <scp>ATP</scp> . Photochemistry and Photobiology, 2013, 89, 1490-1496.	2.5	5
30	Molecular Motion Induced by Multivibronic Excitation on Semiconductor Surface. Journal of Physical Chemistry C, 2014, 118, 1554-1559.	3.1	5
31	Construction and Evaluation of a Miniature Electron Ion Coincidence Analyzer Mounted on a Conflat Flange with an Outer Diameter of 114 mm. Analytical Sciences, 2008, 24, 87-92.	1.6	4
32	The Reaction Process of Firefly Bioluminescence Triggered by Photolysis of Caged-ATP. Photochemistry and Photobiology, 2011, 87, 653-658.	2.5	4
33	Study of Local Valence Electronic States of SiO2Ultrathin Films Grown on Si(111) by Using Auger Photoelectron Coincidence Spectroscopy: Upward Shift of Valence-Band Maximum Depending on the Interface Structure. Journal of the Physical Society of Japan, 2012, 81, 074706.	1.6	4
34	Local Valence Electronic States of SiO2 Ultrathin Films Grown on Si(100) Studied Using Auger Photoelectron Coincidence Spectroscopy: Observation of Upward Shift of Valence-Band Maximum as a Function of SiO2 Thickness. Journal of the Physical Society of Japan, 2011, 80, 084703.	1.6	3
35	Contribution in Semiconductor Industry of Surface Science -Clusters Observed for Adsorbate Coverages Close to the Saturation Coverage Hyomen Kagaku, 2011, 32, 302-307.	0.0	3
36	Surface modification of Cl-adsorbed Si(111)-7×7 by the irradiation of infrared pulsed laser. Surface Science, 2004, 566-568, 1137-1142.	1.9	2

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37	On the resonant SHG response of ultra-thin alkali (K, Rb)-covered Si(111)-7×7. Applied Surface Science, 2011, 257, 3758-3762.	6.1	2
38	Vacuum-ultraviolet reflectance difference spectroscopy for characterizing dielectrics–semiconductor interfaces. Thin Solid Films, 2011, 519, 2830-2833.	1.8	2
39	SHG enhancement by roughness-induced surface plasmon excitation in alkali-metal overlayers grown on Si(111)-7×7. Applied Surface Science, 2013, 267, 58-61.	6.1	2
40	Oxynitride Formation Processes on Si(001) Studied by Means of Reflectance Difference Spectroscopy. Japanese Journal of Applied Physics, 2013, 52, 126505.	1.5	2
41	Decay Processes of Si 2sCore Holes in Si(111)-7 × 7 Revealed by Si Auger Electron Si 2sPhotoelectron Coincidence Measurements. Journal of the Physical Society of Japan, 2014, 83, 094704.	1.6	2
42	Study of Si(111) Surface Reflection Spectrum by Cluster Calculation. Shinku/Journal of the Vacuum Society of Japan, 2006, 49, 138-140.	0.2	2
43	Dependence of Surface Differential Reflectance Spectra on the Incident Photon Energy during Initial Oxidation on Si(001). Shinku/Journal of the Vacuum Society of Japan, 2006, 49, 323-326.	0.2	2
44	K-induced surface structural change of Si(111)-7×7 probed by second-harmonic generation. Applied Surface Science, 2006, 252, 5296-5299.	6.1	1
45	Observation of the adsorption and desorption kinetics of weakly bound CO on Si(001)-c(4×2) by means of reflectance difference spectroscopy. Surface Science, 2017, 662, 82-86.	1.9	1
46	Second-harmonic generation from supported carbon nanotube films grown by chemical vapor deposition on fused silica. Japanese Journal of Applied Physics, 2019, 58, 032006.	1.5	1
47	Real-time Analysis of Initial Oxidation Process on Si(001) by Means of Surface Differential Reflectance Spectroscopy and Reflectance Difference Spectroscopy. Journal of the Vacuum Society of Japan, 2010, 53, 413-420.	0.3	1
48	Simple Low-Outgassing Atomic Hydrogen Source. Journal of the Vacuum Society of Japan, 2012, 55, 403-404.	0.3	1
49	1P269 Time dependence of firefly bioluminescence induced by the photoresolution of caged-ATP(Photobiology:Vision & Photoreception,The 48th Annual Meeting of the Biophysical) Tj ETQq1 1	0.7 <b>84</b> 314	rgBJT /Overlo
50	Auger electron spectra of hydrogenated Si(111)-1×1 surface obtained from <i>Si-L</i> <sub>23</sub> <i>VV</i> Auger electron Si-2 <i>p</i> photoelectron coincidence measurements. Journal of Physics: Conference Series, 2011, 288, 012016.	0.4	0
51	2PT186 Time Dependent Characteristics of Firefly Bioluminescence Initiated by Two Methods with Usual ATP Injection and Photolysis of Caged-ATP(The 50th Annual Meeting of the Biophysical Society of) Tj ETQ	q1 <b>b.0.7</b> 84	431 <b>4</b> rgBT /O
52	Time-resolved chemiluminescence of firefly luciferin generated by dissolving oxygen in deoxygenated dimethyl sulfoxide containing potassium <i>tert</i> -butoxide. Biophysics and Physicobiology, 2015, 12, 69-78.	1.0	0
53	Characterization of effective mobility by split C-V technique in MoS2 MOSFETs with high-k/metal gate. , 2015, , .		0
54	Formation Process of Poly-bromides in Br Adsorption on Si(111) Surface. Shinku/Journal of the Vacuum Society of Japan, 2006, 49, 144-146.	0.2	0

#	Article	IF	CITATIONS
55	Desorption Induced by Excited Electrons from Semiconductor Surfaces (I)-Desorption Induced by Electron-/hole-injection into Halogen-adsorbed Silicon Surfaces Shinku/Journal of the Vacuum Society of Japan, 2006, 49, 600-604.	0.2	0
56	TIME-RESOLVED MEASUREMENT OF FIREFLY BIOLUMINESCENCE USING PHOTOLYSIS OF CAGED-ATP. , 2007, , .		0
57	Real-time Optical Measurement of Alkali-metal Adsorption and Desorption Processes on a Si(001) Surface. Journal of the Vacuum Society of Japan, 2011, 54, 220-223.	0.3	0
58	Attempts to Improve the Sensitivity and the Energy Resolution of an Analyzer for Auger Photoelectron Coincidence Spectroscopy and Electron Ion Coincidence Spectroscopy. Journal of the Vacuum Society of Japan, 2013, 56, 507-510.	0.3	0
59	Real-Time Analysis of Initial Oxidation Process on Si(001) by Means of Surface Differential Reflectance Spectroscopy and Reflectance Difference Spectroscopy. Springer Series in Optical Sciences, 2014, , 29-44.	0.7	0
60	Temporally Resolved Spectroscopy of Laser Ablation of NiO Shinku/Journal of the Vacuum Society of Japan, 1998, 41, 262-265.	0.2	0
61	Thermal oxidation process on Si(113)-(3 × 2) investigated using high-temperature scanning tunneling microscopy. Beilstein Journal of Nanotechnology, 2022, 13, 172-181.	2.8	0